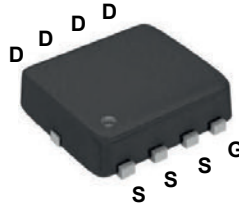
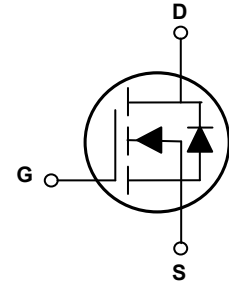


Main Product Characteristics

$V_{(BR)DSS}$	30V
$R_{DS(ON)}$	6.8m Ω (Max.)
I_D	42A



PPAK3x3



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSGN6R803 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, @ Steady-State ($T_C=25^\circ\text{C}$)	I_D	42	A
Continuous Drain Current, @ Steady-State ($T_C=100^\circ\text{C}$)		29	A
Pulsed Drain Current ($T_C=25^\circ\text{C}$) ¹	I_{DM}	168	A
Power Dissipation ($T_C=25^\circ\text{C}$) ²	P_D	22	W
Single Pulse Avalanche Energy ⁵	E_{AS}	33.6	mJ
Single Pulse Current	I_{AS}	11.6	A
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Junction-to-Case	$R_{\theta JC}$	5.68	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	$^\circ\text{C}$
Soldering Temperature (SMD)	T_{sold}	260	$^\circ\text{C}$


Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1.0	μA
		$V_{DS}=30V, V_{GS}=0V, T_J=125^\circ\text{C}$	-	2.0	-	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
Static Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10A$	-	5.3	6.8	m Ω
		$V_{GS}=4.5V, I_D=8A$	-	7.7	10	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	-	2.5	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=15V, f=1\text{MHz}$	-	865	-	μF
Output Capacitance	C_{oss}		-	497	-	
Reverse Transfer Capacitance	C_{rss}		-	35	-	
Total Gate Charge ^{3,4}	Q_g	$I_D=20A, V_{DD}=15V, V_{GS}=10V$	-	16.2	-	nC
Gate-to-Source Charge ^{3,4}	Q_{gs}		-	3.4	-	
Gate-to-Drain ("Miller") Charge ^{3,4}	Q_{gd}		-	2.3	-	
Gate to Plateau ^{3,4}	$V_{plateau}$		-	3.4	-	V
Turn-on Delay Time ^{3,4}	$t_{d(on)}$	$V_{DD}=20V, V_{GS}=10V, R_G=3\Omega, I_D=9A$	-	4.4	-	nS
Rise Time ^{3,4}	t_r		-	31	-	
Turn-Off Delay Time ^{3,4}	$t_{d(off)}$		-	21	-	
Fall Time ^{3,4}	t_f		-	12	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	2.3	-	Ω
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	42	A
Diode Pulse Current	$I_{S,pulse}$		-	-	168	A
Diode Forward Voltage	V_{SD}	$I_S=5A, V_{GS}=0V$	-	-	1.4	V
Reverse Recovery Time ³	T_{rr}	$I_S=2A, V_{GS}=0V, V_R=30V, di_f/dt=100A/\mu s$	-	30	-	nS
Reverse Recovery Charge ³	Q_{rr}		-	15	-	nC

Notes:

- Pulse time of $5\mu s$.
- The dissipated power value will change with the temperature. When it is greater than 25°C , the dissipated power value will decrease by 0.55°C/W for every 1 degree of temperature increase.
- Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Basically unaffected by operating temperature.
- $L=0.5\text{mH}, R_G=25\Omega, V_{DD}=24V, T_J=25^\circ\text{C}$.

Typical Electrical and Thermal Characteristic Curves

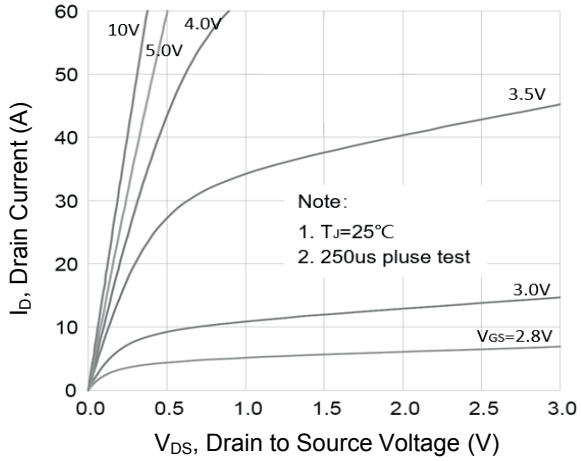


Figure 1. Typical Output Characteristics

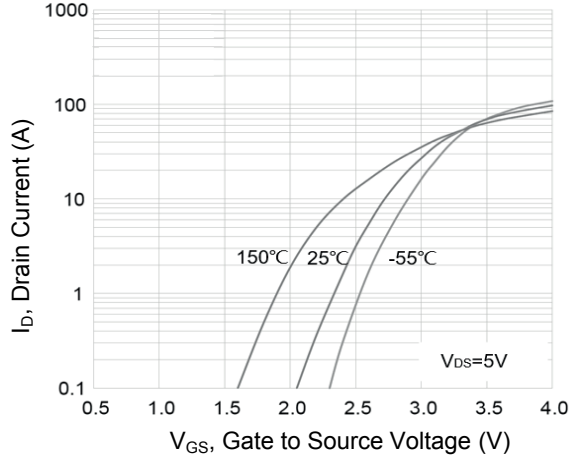


Figure 2. Transfer Characteristics

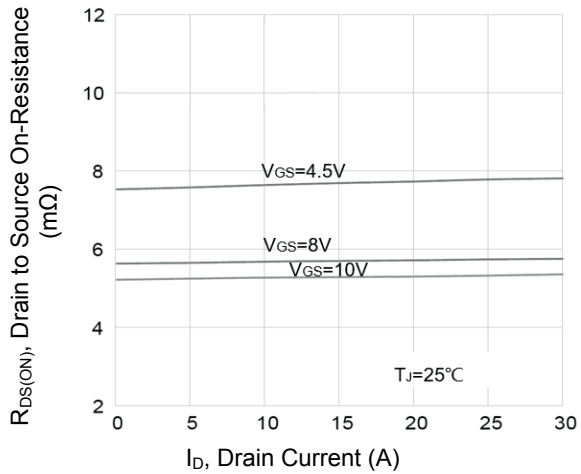


Figure 3. $R_{DS(ON)}$ vs. Drain Current

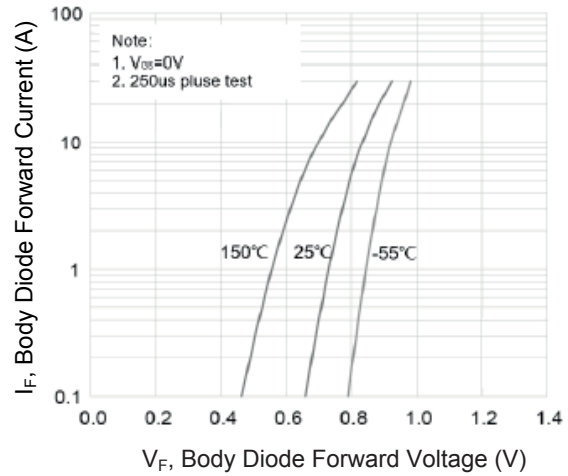


Figure 4. Body Diode Characteristics

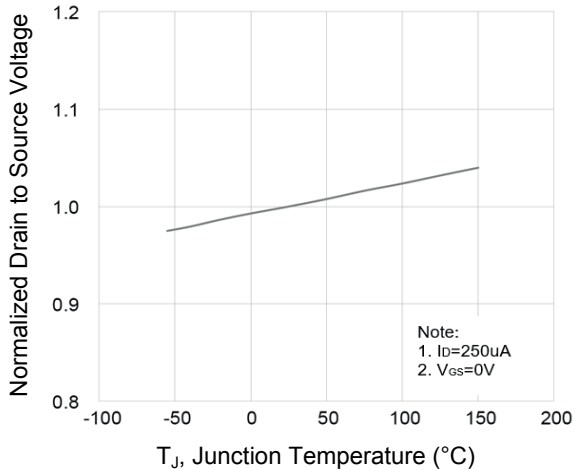


Figure 5. Normalized BV_{DSS} vs. T_J

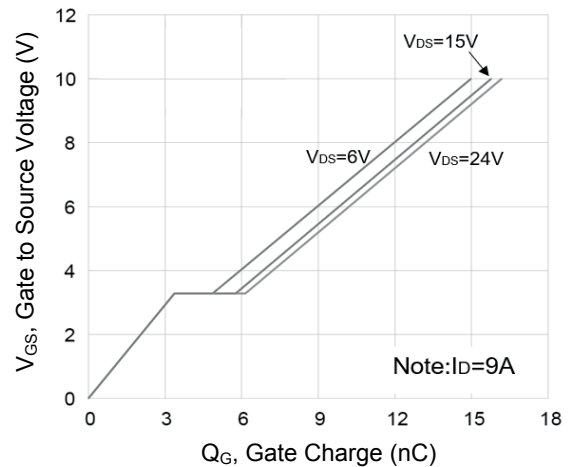
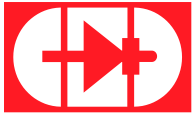


Figure 6. Gate Charge



Typical Electrical and Thermal Characteristic Curves

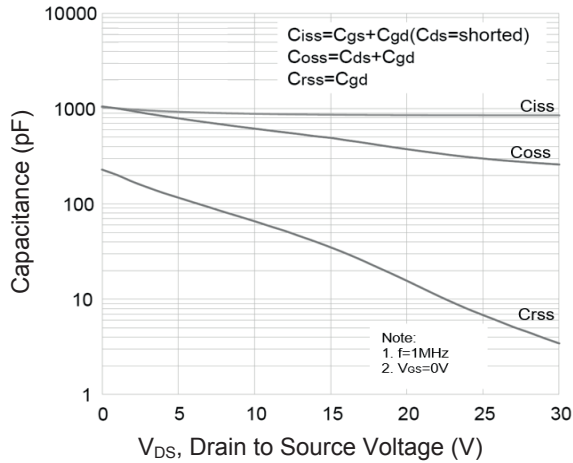


Figure 7. Capacitance Characteristics

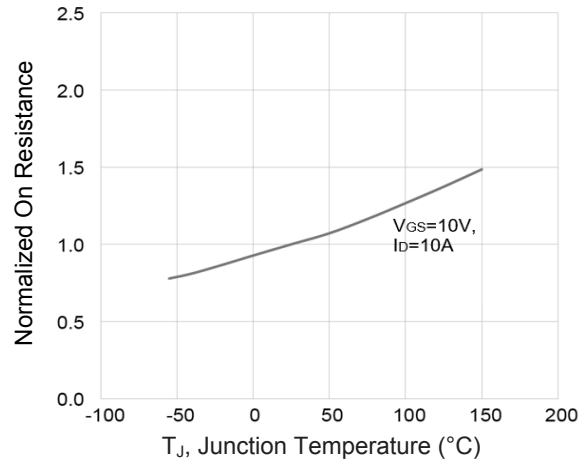


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

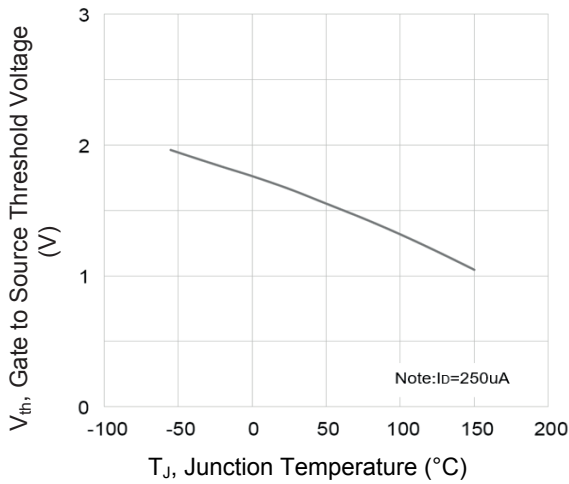


Figure 9. V_{th} vs. T_J

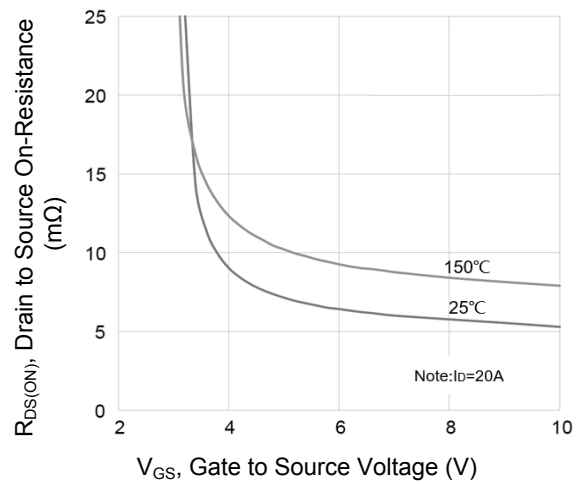
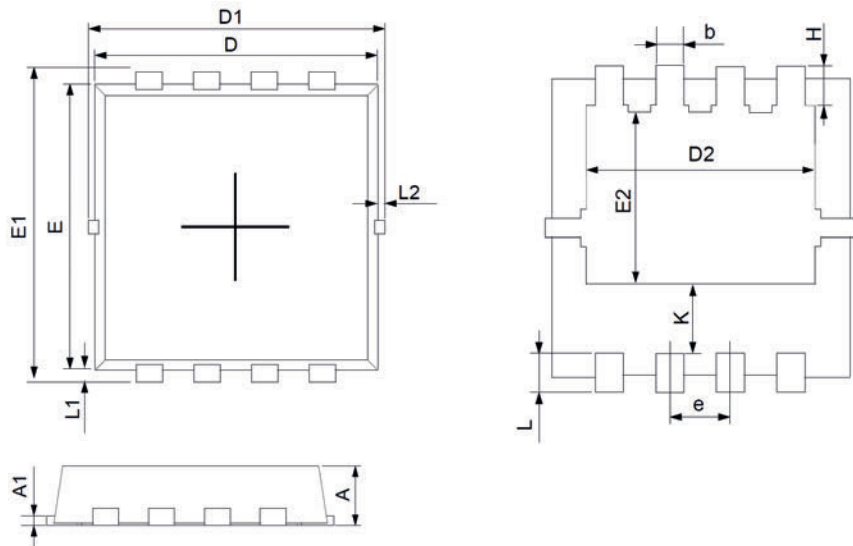


Figure 10. $R_{DS(ON)}$ vs. Gate to Source Voltage

Package Outline Dimensions (PPAK3x3)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.70	0.90	0.028	0.035
A1	0.14	0.20	0.006	0.008
D	3.05	3.25	0.120	0.128
E	2.90	3.10	0.114	0.122
D1	3.10	3.50	0.122	0.138
D2	2.35	2.50	0.093	0.098
E1	3.10	3.50	0.122	0.138
E2	1.64	1.84	0.065	0.072
b	0.25	0.35	0.010	0.014
k	0.59	0.79	0.023	0.031
e	0.55	0.75	0.022	0.030
E4	3.34	3.92	0.131	0.154
L	0.25	0.55	0.010	0.022
L1	0.10	0.20	0.004	0.008
H	0.32	0.52	0.013	0.020

Order Information

Device	Package	Marking	Carrier	Quantity
GSGN6R803	PPAK3x3	N6R803	Tape & Reel	5,000pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com